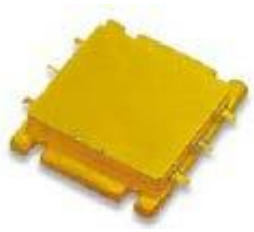
Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 0.8~4.0GHz
- Typical Pout : >49dBm(CW)
- Typical Gain: >11dB
- Typical PAE: >45%
- Bias: 28V/-2V
- Package: Metal Ceramic

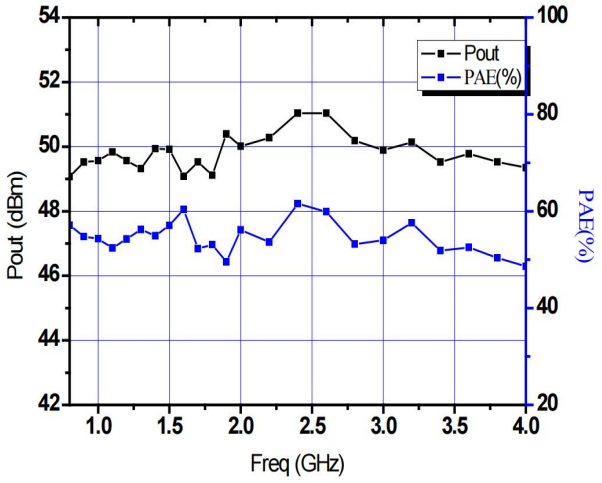


Electrical Specifications (T_A=25℃,V_d=28V,Idq≈1A,F: 0.8~4.0GHz,Pin=38dBm)

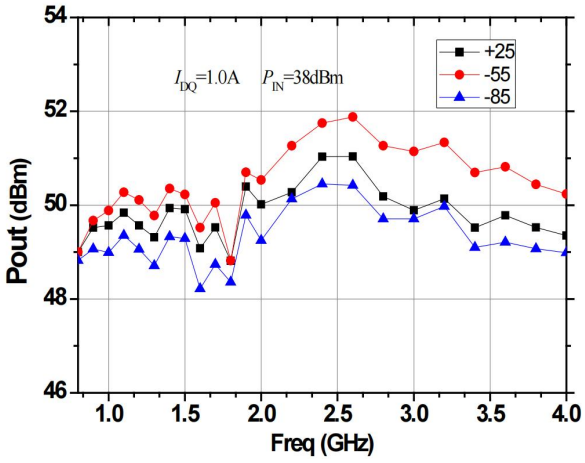
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	49	-	dBm
Gp	Power Gain	-	11	-	dB
ηadd	Power Added Efficiency	-	50	-	%
△Gp	Gain Flatness	-1.2	-	+1.2	dB
Rf2	Second Harmonic	10			dBc
Rth	Thermal Resistance	-	0.95	-	℃/W

Test Curves

Pout、PAE&Freq.



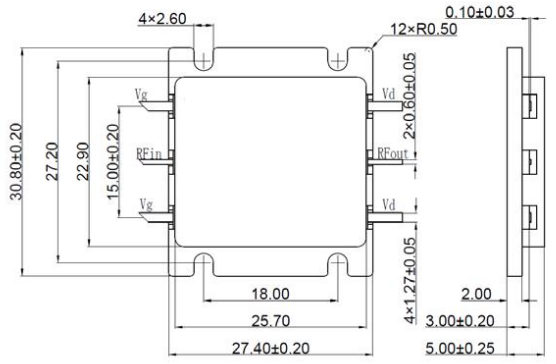
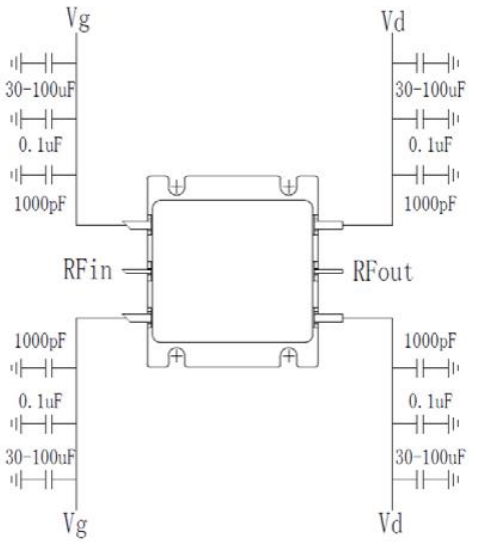
Pout&Freq. @ Different Temp.



Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	250W	25℃
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Application Circuit
	

Note:

(1) This product is an internal matching tube, the input and output resistance values are 50 ohms, and the built-in DC blocking capacitor does not need to be added;

(2) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;

(3) This product is a high-power device. It is necessary to pay attention to heat dissipation during use. The higher the case temperature, the shorter the service life. It is advisable to use the temperature not higher than 80 degrees;

(4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.

(5) The input standing wave is relatively high, and the input terminal needs to be connected to an isolator